

# STX817

## PNP MEDIUM POWER TRANSISTOR

Туре	Marking		
STX817	X817		

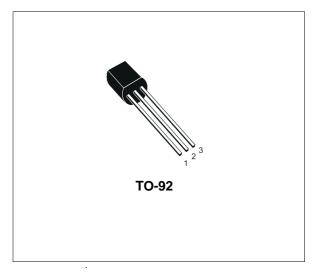
 DEVICE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY

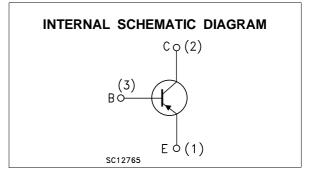
#### **APPLICATIONS**

- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

#### DECRIPTION

The STX817 is a PNP transistor manufactured using Planar Technology resulting in rugged high performance devices.





#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage $(I_E = 0)$	-120	V	
Vceo	Collector-Emitter Voltage (I <sub>B</sub> = 0)	-80	V	
$V_{EBO}$	Emitter-Base Voltage (I <sub>C</sub> = 0)	-5	V	
Ιc	Collector Current	-1.5	А	
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	-2	А	
Ι <sub>Β</sub>	Base Current	-0.3	А	
Івм	Base Peak Current (t <sub>p</sub> < 5 ms)	-0.6	А	
P <sub>tot</sub>	Total Dissipation at $T_{amb} = 25 \ ^{\circ}C$	0.9	W	
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	44.6	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	139	°C/W

### **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

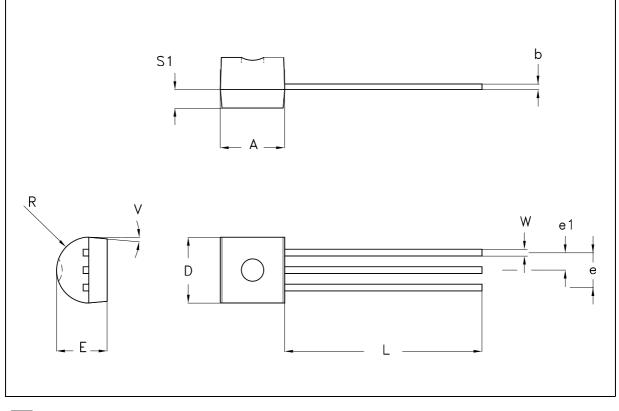
Symbol	Parameter	Test Co	onditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = -120 V				-500	μA
I <sub>CEO</sub>	Collector Cut-off Current ( $I_B = 0$ )	V <sub>CE</sub> = -80 V				-1	mA
I <sub>EBO</sub>	Emitter Cut-off Current $(I_C = 0)$	V <sub>EB</sub> = -5 V				-100	μA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage $(I_B = 0)$	I <sub>C</sub> = -10 mA		-80			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100 mA I <sub>C</sub> = -1 A	I <sub>B</sub> = -10 mA I <sub>B</sub> = -100 mA			-0.25 -0.5	V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = -100 mA I <sub>C</sub> = -1 A	I <sub>B</sub> = -10 mA I <sub>B</sub> = -100 mA			-1 -1.1	V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = -100 mA I <sub>C</sub> = -500 mA I <sub>C</sub> = -1 A	V <sub>CE</sub> = -2 V V <sub>CE</sub> = -2 V V <sub>CE</sub> = -2 V	140 80 40			
f⊤	Transition Frequency	I <sub>C</sub> = -0.1 A	$V_{CE} = -10 V$		50		MHz

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

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DIM.		mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.32		4.95	0.170		0.195	
b	0.36		0.51	0.014		0.020	
D	4.45		4.95	0.175		0.194	
E	3.30		3.94	0.130		0.155	
е	2.41		2.67	0.095		0.105	
e1	1.14		1.40	0.045		0.055	
L	12.70		15.49	0.500		0.609	
R	2.16		2.41	0.085		0.094	
S1	1.14		1.52	0.045		0.059	
W	0.41		0.56	0.016		0.022	
V	4 degree		6 degree	4 degree		6 degree	





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